

FORM PTO-1449 (Modified) U.S. Department of Commerce, Patent and Trademark Office				Docket No. <u>02-5624</u>	Serial No. <u>W/676 934</u>
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicants <u>Byung-Sung Kwak et al.</u>	
				Filing Date Herewith	Group Unknown <u>2823</u>

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<u>TWP</u>	AA	5,874,367	2/23/99	Dobson	438	787	
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents

Translation

		Document Number	Date	Country	Class	Subclass	Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>TWP</u>	AR	Bothra, S., et al., "Integration of 0.25 μm Three and Five Level Interconnect System for High Performance ASIC", <u>1997 Proceedings Fourteenth International VMIC Conference</u> , Santa Clara, CA, June 10-12, 1997, pp.43-48.
<u>TWP</u>	AS	Brongersma, S.H., et al., 'Non-Correlated Behavior of Sheet Resistance and Stress During Self-Annealing of Electroplated Copper", <u>IITC</u> , 1999, pp. 290-292.
<u>TWP</u>	AT	Dobson, C.D., et al., "Advanced SiO ₂ Planarization Using Silane and H ₂ O ₂ ", <u>Semiconductor International</u> , December 1994, pp. 85-88.

Examiner Jhamka Manku Date Considered 9/27/04

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	BC						
	BD						
	BE						
	BF						
	BG						
	BH						
	BI						
	BJ						
	BK						

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	BL							
	BM							
	BN							
	BO							
	BP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

TWP	BR	Hau-Riege, Stefan P., Handbook entitled "Copper Interconnect Technology", University of California-Berkeley Extension Course, April, 2002, pp. 129-137.
TWP	BS	Kittel, Charles, <u>Introduction to Solid State Physics</u> , 6th ed., New York: John Wiley & Sons, 1986, pp. 143, 145.
TWP	BT	McClatchie, S., et al., "Low Dielectric Constant Oxide Films Deposited Using CVD Techniques", 1998 Proceedings Fourth International DUMIC Conference, February 16-17, 1998, pp. 311-318.

Examiner
J. Hamman

Date Considered 2/27/04

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	CA						
	CB						
	CC						
	CD						
	CE						
	CF						
	CG						
	CH						
	CI						
	CJ						
	CK						

Foreign Patent Documents

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		Document Number	Date	Country	Class	Subclass	Yes	No
	CL							
	CM							
	CN							
	CO							
	CP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

WP	CR	Peters, Laura, "Low-k Dielectrics: Will Spin-On or CVD Prevail?", <u>Semiconductor International</u> , Vol. 23, No. 6, June, 2000, pp. 108-110, 114, 116, 118, 122, and 124.
WP	CS	Peters, Laura, "Pursuing the Perfect Low-k Dielectric", <u>Semiconductor International</u> , Vol. 21, No. 10, September, 1998, pp. 64-66, 68, 70, 72, and 74.
WP	CT	Ramanan, V.R.V., et al., "Crystallization Kinetics in Fe-B-Si Metallic Glasses", <u>J. Appl. Phys.</u> , Vol. 53, No. 3, March, 1982, pp. 2273-2275.

Examiner
unnamelnameDate Considered 27/07

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	DA						
	DB						
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	DD						
	DE						
	DF						
	DG						
	DH						
	DI						
	DJ						
	DK						

Foreign Patent Documents

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	DL							
	DM							
	DN							
	DO							
	DP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

TWP	DR	Ritzdorf, T., et al., "Comparative Investigation of Plating Conditions on Self-Annealing of Electrochemically Deposited Copper Films", <u>IITC</u> , 1999, pp. 287-289.
TWP	DS	Rossnagel, S.M., et al., "From PVD to CVD to ALD for Interconnects and Related Applications", <u>IITC</u> , 2001, p. 2.
	DT	

Examiner <i>John Han</i>	Date Considered <i>9/27/07</i>
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